

# **NCE N-Channel Super Trench II Power MOSFET**

## **Description**

The series of devices uses **Super Trench II** technology that is uniquely optimized to provide the most efficient high frequency switching performance. Both conduction and switching power losses are minimized due to an extremely low combination of  $R_{\text{DS(ON)}}$  and  $Q_g$ . This device is ideal for high-frequency switching and synchronous rectification.

# **Application**

- DC/DC Converter
- •Ideal for high-frequency switching and synchronous rectification

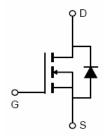
#### **General Features**

- $V_{DS}$  =100V, $I_D$  =62A  $R_{DS(ON)}$ =4.4m $\Omega$  , typical @  $V_{GS}$ =10V
- Excellent gate charge x R<sub>DS(on)</sub> product(FOM)
- Very low on-resistance R<sub>DS(on)</sub>
- 175 °C operating temperature
- Pb-free lead plating

100% UIS TESTED! 100% ΔVds TESTED!

**TO-220F** 





**Schematic Diagram** 

# **Package Marking and Ordering Information**

| 1 |                |             |                |           |            |          |
|---|----------------|-------------|----------------|-----------|------------|----------|
|   | Device Marking | Device      | Device Package | Reel Size | Tape width | Quantity |
|   | NCEP039N10F    | NCEP039N10F | TO-220F        | -         | -          | -        |

Absolute Maximum Ratings (T<sub>C</sub>=25 ℃unless otherwise noted)

| Parameter  | Symbol                | Limit      | Unit          |
|--|-----------------------|------------|---------------|
| Drain-Source Voltage                             | VDS                   | 100        | V             |
| Gate-Source Voltage                              | V <sub>G</sub> s      | ±20        | V             |
| Drain Current-Continuous (Package Limited)       | I <sub>D</sub>        | 62         | Α             |
| Drain Current-Continuous(T <sub>C</sub> =100°C)  | I <sub>D</sub> (100℃) | 45         | Α             |
| Pulsed Drain Current (Note 1)                    | I <sub>DM</sub>       | 248        | Α             |
| Maximum Power Dissipation                        | P <sub>D</sub>        | 40         | W             |
| Derating factor                                  |                       | 0.27       | W/℃           |
| Avalanche Current <sup>(Note 1)</sup>            | I <sub>AR</sub>       | 55         | Α             |
| Single pulse avalanche energy (Note 5)           | E <sub>AS</sub>       | 1156       | mJ            |
| Operating Junction and Storage Temperature Range | $T_{J}, T_{STG}$      | -55 To 175 | ${\mathbb C}$ |

#### **Thermal Characteristic**

| Thermal Resistance, Junction-to-Case (Note 2) | $R_{	heta JC}$ | 3.75 | °C/W |
|---|----------------|------|------|



Electrical Characteristics (T<sub>C</sub>=25 °C unless otherwise noted)

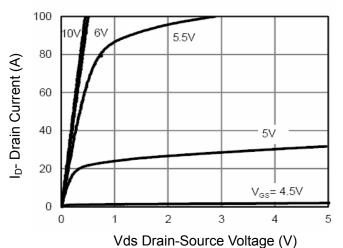
| Parameter                          | Symbol              | Condition   | Min | Тур  | Max  | Unit |
|------------------------------------|---------------------|---|-----|------|------|------|
| Off Characteristics                |                     |   |     | •    |      |      |
| Drain-Source Breakdown Voltage     | BV <sub>DSS</sub>   | V <sub>GS</sub> =0V I <sub>D</sub> =250μA               | 100 |      | -    | V    |
| Zero Gate Voltage Drain Current    | I <sub>DSS</sub>    | V <sub>DS</sub> =100V,V <sub>GS</sub> =0V               | -   | -    | 1    | μA   |
| Gate-Body Leakage Current          | I <sub>GSS</sub>    | V <sub>GS</sub> =±20V,V <sub>DS</sub> =0V               | -   | -    | ±100 | nA   |
| On Characteristics (Note 3)        |                     |   | •   |      |      | •    |
| Gate Threshold Voltage             | V <sub>GS(th)</sub> | V <sub>DS</sub> =V <sub>GS</sub> ,I <sub>D</sub> =250μA | 2.0 | 3.0  | 4.0  | V    |
| Drain-Source On-State Resistance   | R <sub>DS(ON)</sub> | V <sub>GS</sub> =10V, I <sub>D</sub> =31A               | -   | 4.4  | 4.8  | mΩ   |
| Forward Transconductance           | <b>g</b> FS         | V <sub>DS</sub> =5V,I <sub>D</sub> =31A                 |     | 90   | -    | S    |
| Dynamic Characteristics (Note4)    |                     |   | •   |      |      | •    |
| Input Capacitance                  | C <sub>lss</sub>    | V 50VVV 0V  | -   | 6400 | -    | PF   |
| Output Capacitance                 | C <sub>oss</sub>    | $V_{DS}$ =50V, $V_{GS}$ =0V,<br>F=1.0MHz                | -   | 585  | -    | PF   |
| Reverse Transfer Capacitance       | C <sub>rss</sub>    | F=1.UMHZ  | -   | 26   | -    | PF   |
| Switching Characteristics (Note 4) |                     |   | •   |      |      | •    |
| Turn-on Delay Time                 | t <sub>d(on)</sub>  |   | -   | 20   | -    | nS   |
| Turn-on Rise Time                  | t <sub>r</sub>      | $V_{DD}$ =50 $V$ , $I_{D}$ =31 $A$                      | -   | 11.5 | -    | nS   |
| Turn-Off Delay Time                | t <sub>d(off)</sub> | $V_{GS}$ =10 $V$ , $R_{G}$ =1.6 $\Omega$                | -   | 48   | -    | nS   |
| Turn-Off Fall Time                 | t <sub>f</sub>      |   | -   | 10   | -    | nS   |
| Total Gate Charge                  | Qg                  | \/ F0\/ L 04A   | -   | 102  | -    | nC   |
| Gate-Source Charge                 | Q <sub>gs</sub>     | $V_{DS}=50V,I_{D}=31A,$                                 | -   | 36   |      | nC   |
| Gate-Drain Charge                  | Q <sub>gd</sub>     | V <sub>GS</sub> =10V                                    | -   | 26   |      | nC   |
| Drain-Source Diode Characteristics |                     |   | •   |      |      |      |
| Diode Forward Voltage (Note 3)     | V <sub>SD</sub>     | V <sub>GS</sub> =0V,I <sub>S</sub> =31A                 | -   |      | 1.2  | V    |
| Diode Forward Current (Note 2)     | Is                  |   | -   | -    | 62   | Α    |
| Reverse Recovery Time              | t <sub>rr</sub>     | $T_J = 25^{\circ}C, I_F = I_S$                          | -   | 76   | -    | nS   |
| Reverse Recovery Charge            | Qrr                 | $di/dt = 100A/\mu s^{(Note3)}$                          | -   | 150  | -    | nC   |

## Notes:

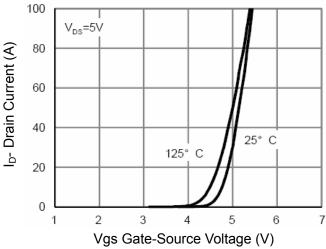
- 1. Repetitive Rating: Pulse width limited by maximum junction temperature.
- 2. Surface Mounted on FR4 Board, t ≤ 10 sec.
- 3. Pulse Test: Pulse Width  $\leq$  300 $\mu$ s, Duty Cycle  $\leq$  2%.
- 4. Guaranteed by design, not subject to production
- 5. EAS condition : Tj=25  $^{\circ}\text{C}$  ,V\_DD=50V,V\_G=10V,L=0.5mH,Rg=25 $\Omega$



# **Typical Electrical and Thermal Characteristics**



**Figure 1 Output Characteristics** 



**Figure 2 Transfer Characteristics** 

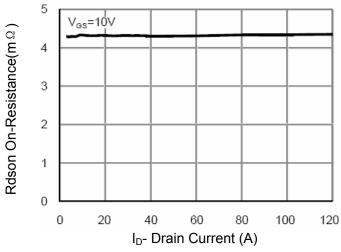
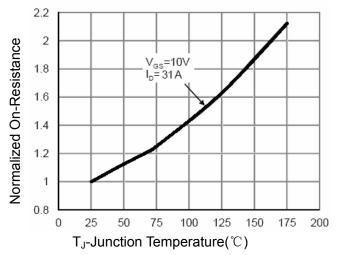


Figure 3 Rdson- Drain Current



**Figure 4 Rdson-Junction Temperature** 

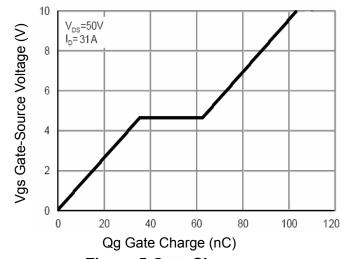


Figure 5 Gate Charge

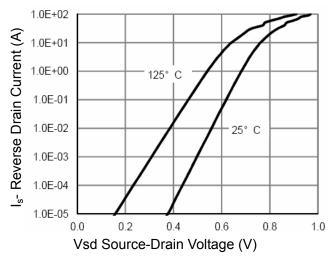


Figure 6 Source- Drain Diode Forward



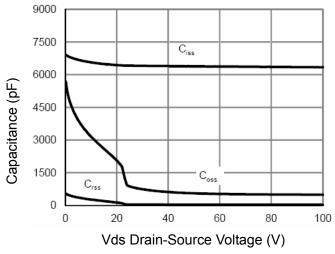


Figure 7 Capacitance vs Vds

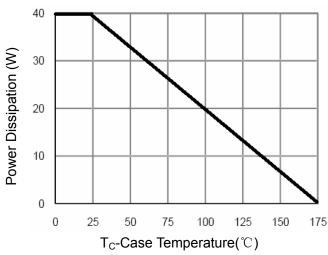
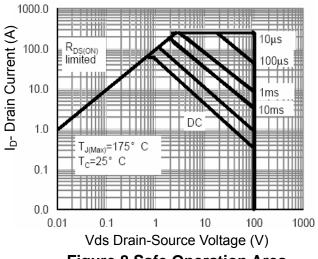


Figure 9 Power De-rating



**Figure 8 Safe Operation Area** 

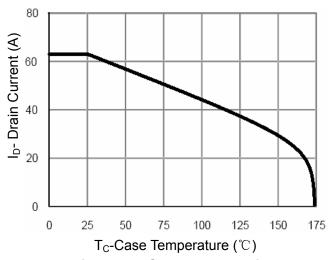
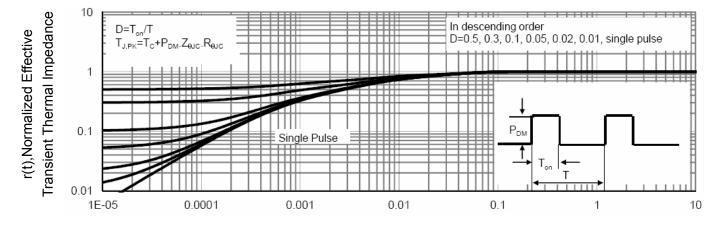


Figure 10 Current De-rating

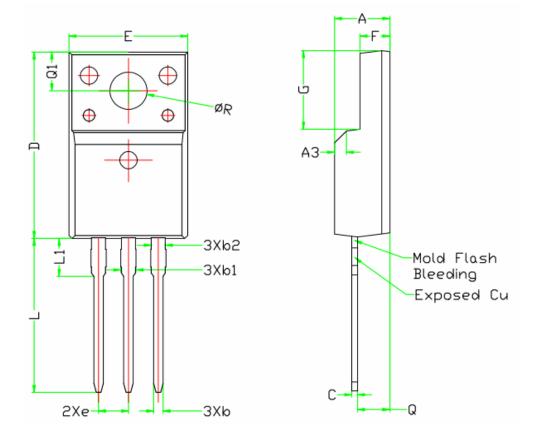


Square Wave Pluse Duration(sec)

**Figure 11 Normalized Maximum Transient Thermal Impedance** 



# **TO-220F Package Information**



|        | DIMENSIONS |       |       |  |  |  |
|--------|------------|-------|-------|--|--|--|
| SYMBOL | Min. Nom.  |       | Max.  |  |  |  |
| A      | 4.60       | 4.70  | 4.80  |  |  |  |
| ь      | 0.70       | 0.80  | 0.91  |  |  |  |
| ь1     | 1.20       | 1.30  | 1.47  |  |  |  |
| b2     | 1.10       | 1.20  | 1.30  |  |  |  |
| С      | 0.45       | 0.50  | 0.63  |  |  |  |
| D      | 15.80      | 15.87 | 15.97 |  |  |  |
|        | 2.54       |       |       |  |  |  |
| E      | 10.00      | 10.10 | 10.30 |  |  |  |
| F      | 2.44       | 2.54  | 2.64  |  |  |  |
| G      | 6.50       | 6.70  | 6.90  |  |  |  |
| L      | 12.90      | 13.10 | 13.30 |  |  |  |
| L1     | 3.13       | 3.23  | 3.33  |  |  |  |
| Q      | 2.65       | 2.75  | 2.85  |  |  |  |
| Q1     | 3.20       | 3.30  | 3.40  |  |  |  |
| ΦR     | 3.06       | 3.18  | 3.28  |  |  |  |



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